

Pb ROHS COMPLIANT

TSM120N10PQ56

100V N-Channel MOSFET

PDFN56

8

Pin Definition:

1. Source	B. Drain
2. Source	7. Drain
3. Source	6. Drain
4. Gate	5. Drain

Key Parameter Performance

Parameter	Value	Unit
V_{DS}	100	V
R _{DS(on)} (max)	12	mΩ
Q_g	145	nC

Features

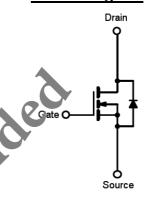
- Low On-Resistance
- Low Input Capacitance
- Low Gate Charge

Ordering Information

Part No.	Package	Packing
TSM120N10PQ56 RLG	PDFN56	2.5kpcs / 13" Reel

Note: "G" denotes for Halogen- and Antimony-free as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Block Diagram



N-Channel MOSFET

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter	-07	Symbol	Limit	Unit	
Drain-Source Voltage			100	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current (Note 3)	T _C =25°C		58	А	
	T _A =25°C	I _D	16.1		
Drain Current-Pulsed (Note 1)		I _{DM}	150	Α	
Single Pulse Avalanche Energy L=0.5mH		E _{AS}	156	mJ	
Maximum Power Dissipation (Note 2)	T _C =25°C	D	36	W	
	T _A =25°C	P_{D}	2		
Storage Temperature Range		T _{STG}	-55 to +150	°C	
Operating Junction Temperature Range		T _J	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	$R_{\Theta JC}$	1.2	°C/W
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	62	°C/W



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Electrical Specifications (T_J=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	100			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 30A$	R _{DS(ON)}		10	12	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V _{GS(TH)}	2	3	4	V
Zero Gate Voltage Drain Current	$V_{DS} = 80V, V_{GS} = 0V$	I _{DSS}			1	μA
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Dynamic						
Total Gate Charge		Q_g	4	145		nC
Gate-Source Charge	$V_{DS} = 50V, I_{D} = 30A,$	Q_{gs}		25		
Gate-Drain Charge	$V_{GS} = 10V$	Q _{gd}		43		
Input Capacitance		C _{iss}		3902		
Output Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1.0MHz	Cos		251		pF
Reverse Transfer Capacitance	7 I = I.UIVITIZ	rss		93		
Switching						
Turn-On Delay Time		t _{d(on)}		27		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 50V,$	t _r		13		
Turn-Off Delay Time	$R_G = 3\Omega$, $I_D = 30A$	t _{d(off)}		15		ns
Turn-Off Fall Time	26	t _f		42		
Drain-Source Diode Characteristics and waximum Rating						
Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =30A	V _{SD}			1.3	V
Reverse Recovery Time	I _S = 30A, dl/dt = 100A/μs	t _{rr}		65		ns
Reverse Recovery Charge	$I_S = 30A$, $uI/uI = 100A/\mu S$	Q_{rr}		175		nC

Notes:

- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air

3. The maximum current is limited by package.

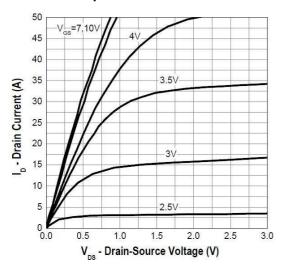


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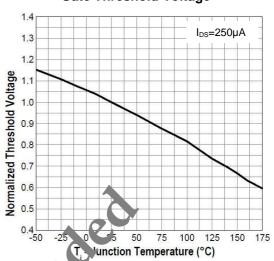


Electrical Characteristics Curves

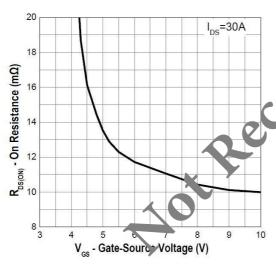
Output Characteristics



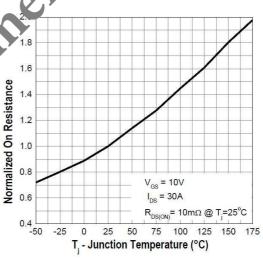
Gate Threshold Voltage



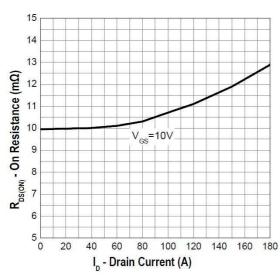
Gate Source On Resistance



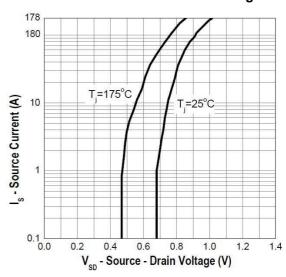
Lain-Source On Resistance



Drain-Source On-Resistance



Source-Drain Diode Forward Voltage

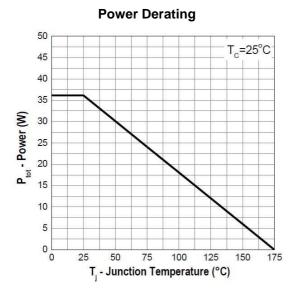




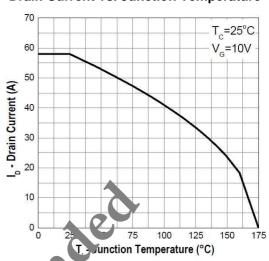
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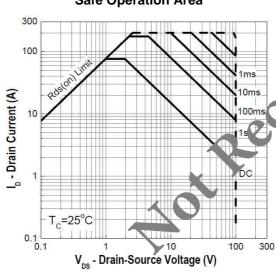
Electrical Characteristics Curves



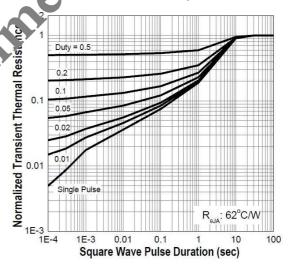
Drain Current vs. Junction Temperature



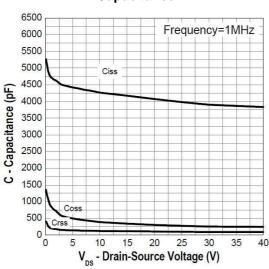




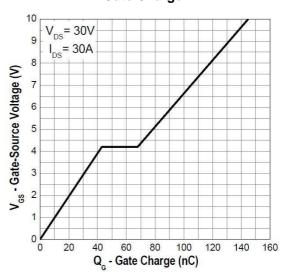
Transient Thermal Impedance



Capacitance



Gate Charge

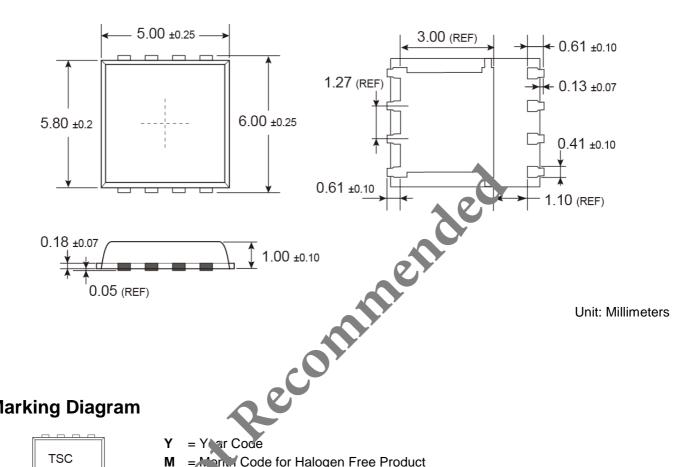




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PDFN56 Mechanical Drawing



Marking Diagram



L = Lot Code

= Y(or Code Υ = Month Code for Halogen Free Product ■Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)



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Aot Recommended

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